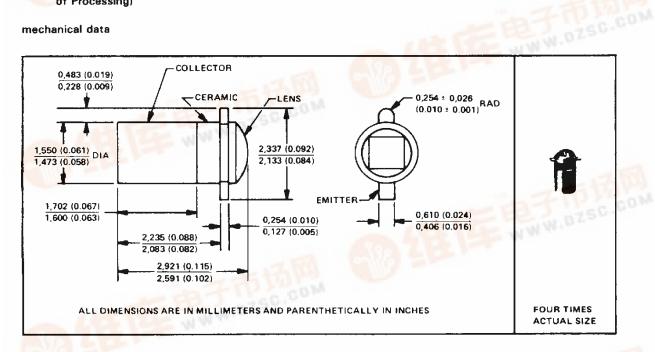
TIL601 THRU TIL604, LS600, LS602, LS611 THRU LS619 N-P-N PLANAR SILICON PHOTOTRANSISTORS

SODS026A D1971, NOVEMBER 1974-REVISED SEPTEMBER 1989 WWW.DZSG.COM

DESIGNED FOR HIGH-DENSITY READ OUT

- Hermetically-Sealed Pill Package
- Recommended for Application in Character Recognition, Tape and Card Readers, Velocity Indicators, and Encoders
- Unique Package Design Allows for Assembly into Printed Circuit Boards
- Spectrally and Mechanically Compatible with TIL23 thru TIL25
- Saturation Level Directly Compatible with Most TTL
- TIL604HR2[†] Includes High-Reliability Processing and Lot Acceptance (See TIL604HR2 for Summary of Processing)

mechanical data



All electrical and mechanical specifications for the TIL24 also apply for TIL24HR2



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absolute maximum ratings at 25 °C case temperature (unless otherwise noted)

Collector-emitter voltage 5	60 V
Emitter-collector voltage	7 V
Continuous device dissipation at (or below) 25 °C case temperature (see Note 1) 50	mW
Operating case temperature range	5°C
Storage temperature range65 °C to 15	0°C
Soldering temperature (10 seconds)	

electrical characteristics at 25 °C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYPE	MIN	TYP	MAX	UNIT
V _(BR) CEO	Collector-emitter breakdown voltage	$I_C = 100 \mu A, E_e = 0$	All	50			V
V(BR)ECO	Emitter-collector breakdown voltage	$I_E = 100 \mu A, E_e = 0$	All	7			>
		V _{CE} = 30 V, E _e = 0	All			25	nΑ
lD	Dark current	$V_{CE} = 30 \text{ V}, E_e = 0,$ $T_{C} = 100 ^{\circ}\text{C}$	Ail		3		μА
	Light current		TIL601	0.5		3	mA
			TIL602	2		5	
			TIL603	4		8	
			TIL604	7			
			LS600	0.8			
			LS602	0.5			
) V _{CE} = 5 V.	2 LS611	0.5	1	2	
IL		VCE = 5 V. Ee = 20 mvv/cm See Note 2	LS612	1	2	3	
		See Note 2	LS613	2	. 3	_ 4	
			LS614	3	4	5	
			LS615	4	5	6	
			LS616	5	6	7	
			LS617	6	_ 7	8	
			L\$618	7	8	9	
			LS619	8	9		
VCE(sat)	Collector-emitter saturation voltage	I _C = 0.4 mA, E _e = 20 mW/cm See Note 2	2 _, All		0.15		٧

NOTES: 1. Denate linearly to 125°C at the rate of 0.5 mW/°C.

 Irradiance (E_e) is the radiant power per unit area incident upon a surface. For this measurement, the source is an unfiltered tungsten linear-filament lamp operating at a color temperature of 2870 K.

switching characteristics at 25 °C case temperature

	PARAMETER	TEST CONDITIONS	TYP	UNIT
t,	Rise time	V _{CC} = 30 V, I _L = 800 дА,	8	
T _f	Fall time	$R_L = 1 k\Omega$, See Figure 1	6	1 μ5

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PARAMETER MEASUREMENT INFORMATION See Note A OUTPUT See Note B V_{CC} * 30 V R_L = 1 kΩ TEST CIRCUIT **OUTPUT VOLTAGE WAVEFORM**

- NOTES: A. Input irradiance is supplied by a pulsed gallium arsenide infrared emitter with rise and fall times of less than 50 ns. Incident rradiation is adjusted for $I_L=800~\mu A$.

 B. Output waveform is monitored on an oscilloscope with the following characteristics: $t_r \le 25~\text{ns}$, $R_{in} \ge 1~\text{M}\Omega$, $C_{in} \le 20~\text{pF}$.

FIGURE 1

TYPICAL APPLICATION DATA – 20 V 40 M Ω 1N756 2N3330 5.6 kΩ 2N3330 15 kΩ - OUTPUT **PHOTOTRANSISTOR** $2.2\,k\Omega$

FIGURE 2. LOW-LEVEL DETECTOR AND PREAMPLIFIER

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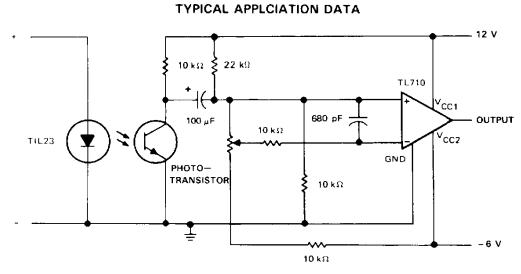


FIGURE 3. OPTICALLY COUPLED AMPLIFIER

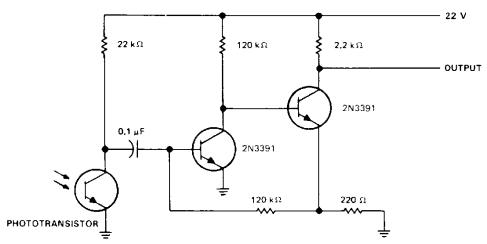


FIGURE 4. LIGHT PULSE DETECTOR

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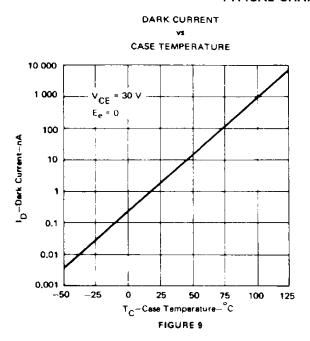
TYPICAL CHARACTERISTICS COLLECTOR CURRENT COLLECTOR CURRENT COLLECTOR-EMITTER VOLTAGE COLLECTOR-EMITTER VOLTAGE 2.4 10 2.2 TIL602 T_C = 25°C T_C = 25°C 2.0 See Note 2 See Note 2 8 1.8 LC-Collector Current-mA I_C-Collector Current-mA 1.6 6 1.4 E_e = 40 mW/cm² = 30 mW/cm² 1.2 $E_P = 60 \text{ mW/cm}^2$ 1.0 4 0.8 $E_P = 20 \text{ mW/cm}^2$ 0.6 2 0.4 20 mW/cm² 0.2 10 mW/cm² 0 0 0.05 0 0.1 0.15 0.2 0.25 0.3 12 20 V_{CE}-Collector-Emitter Voltage-V $V_{CE}^{-Collector-Emitter\ Voltage-V}$ FIGURE 5 FIGURE 6 COLLECTOR-EMITTER SATURATION VOLTAGE COLLECTOR CURRENT ¥5 IRRADIANCE IRRADIANCE 0.24 4.0 I_C = 0.5 mA VCE(set) - Collector-Emitter Saturation Voltage-V T_C = 25°C T1L602 T_C = 25°C 3.5 See Note 2 0.20 See Note 2 3.0 I_C-Collector Current-mA ${\bf v}_{\rm CE}$ 0,16 2.5 ~ 0.3 V v_{CE} 0.12 2.0 VCE v_{CE} 1.5 0.08 1.0 0.04 0.5 0 0 20 70 80 0 30 50 60 10 15 20 E_e -Irradiance mW/cm² $E_e{=}\mathsf{Irradiance}/\mathsf{mW/cm^2}$ FIGURE 7 FIGURE 8

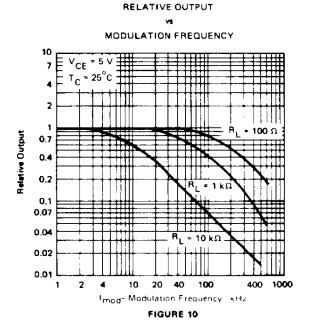
NOTE 2. Irradiance (Eg) is the radiant power unit area incident upon a surface. For this measurement, the source is an unfiltered tungsten linear-filament lamp operating at a color temperature of 2870 K.



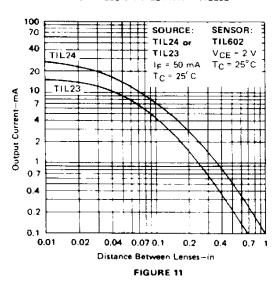
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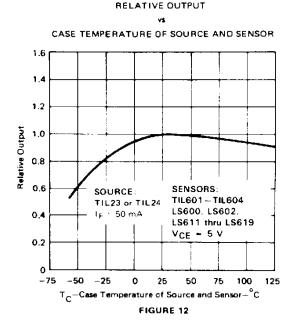
TYPICAL CHARACTERISTICS





COUPLING CHARACTERISTICS
OF TIL23 OR TIL24 WITH TIL602

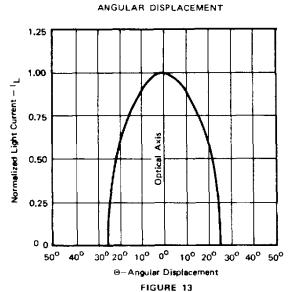




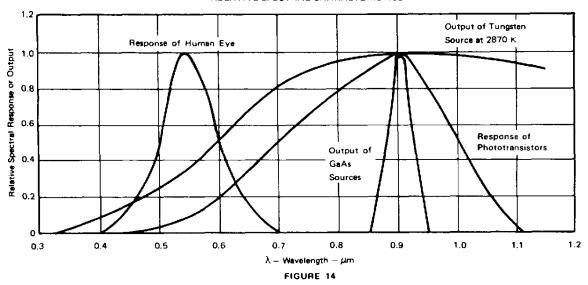
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TYPICAL CHARACTERISTICS

NORMALIZED LIGHT CURRENT vs



RELATIVE SPECTRAL CHARACTERISTICS



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